# **Hex Buffer**

The MC74VHC50 is an advanced high speed CMOS buffer fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $t_{PD} = 3.8 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A$  (Max) at  $T_A = 25$ °C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.8 V (Max)
- These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

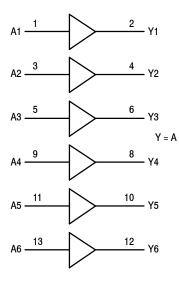


Figure 1. Logic Diagram

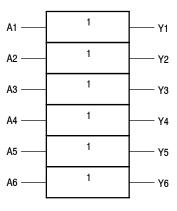


Figure 2. Logic Symbol



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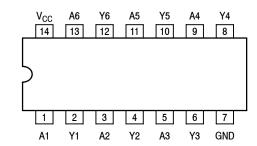


14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G



14-LEAD SOIC EIAJ M SUFFIX CASE 965

# PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

# **FUNCTION TABLE**

Y Output
L
Н

## **ORDERING INFORMATION**

Device	Package	Shipping
MC74VHC50D	SOIC	55 Units/Rail
MC74VHC50M	SOIC EIAJ	50 Units/Rail

## **MAXIMUM RATINGS**

Symbol		Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to $V_{CC} + 0.5$	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>O</sub> < GND	± 20	mA
l <sub>OUT</sub>	DC Output Sink Current		± 25	mA
Icc	DC Supply Current per Supply Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range		−65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Cas	e for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{JA}$	Thermal Resistance	(Note 1) SOIC TSSOP	125 170	°C/W
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30 to 35	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 2000	V
I <sub>Latch-Up</sub>	Latch-Up Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Supply Voltage	2.0	5.5	V
VI	Input Voltage (Note 6)	0	5.5	V
V <sub>O</sub>	Output Voltage (HIGH or LOW State)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Free-Air Temperature	<b>–</b> 55	+ 125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $ V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}                                  $	0 0	100 20	ns/V

<sup>6.</sup> Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

NOTE: The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

# DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	7	Γ <sub>A</sub> = 25°(	2	T <sub>A</sub> ≤	85°C	T <sub>A</sub> ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.0 3.15 3.85			1.5 2.0 3.15 3.85		1.5 2.0 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40	μΑ

# AC ELECTRICAL CHARACTERISTICS ( $C_{load}$ = 50 pF, Input $t_r$ = $t_f$ = 3.0 ns)

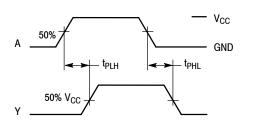
				T <sub>A</sub> = 25°C		T <sub>A</sub> ≤ 85°C		T <sub>A</sub> ≤ 125°C			
Symbol	Parameter	Parameter Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit	
t <sub>PHL</sub> Propo	Maximum Propogation Delay,	$V_{CC} = 3.0 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		5.0 7.5	7.1 10.6		8.5 12.0		10.0 14.5	ns
	Input A to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.8 5.3	5.5 7.5		6.5 8.5		8.0 10.0	
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10		10	pF

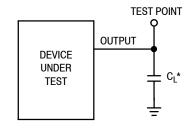
		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note 7)	18	pF

<sup>7.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# NOISE CHARACTERISTICS (Input $t_{f}$ = $t_{f}$ = 3.0 ns, $C_{L}$ = 50 pF, $V_{CC}$ = 5.0 V)

		T <sub>A</sub> =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.8	1.0	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.8	-1.0	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V





\*Includes all probe and jig capacitance
Figure 4. Test Circuit

Figure 3. Switching Waveforms

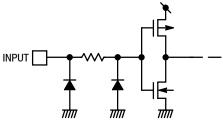
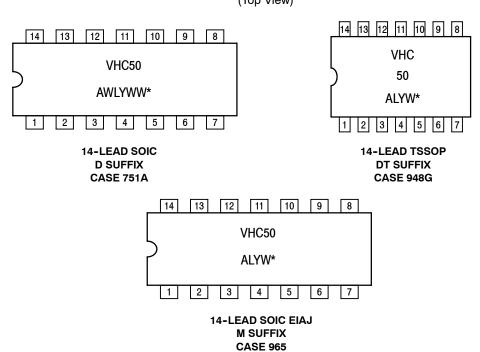


Figure 5. Input Equivalent Circuit

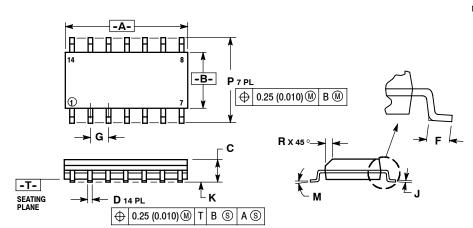
# MARKING DIAGRAMS (Top View)



\*See Applications Note #AND8004/D for date code and traceability information.

# **PACKAGE DIMENSIONS**

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE F** 

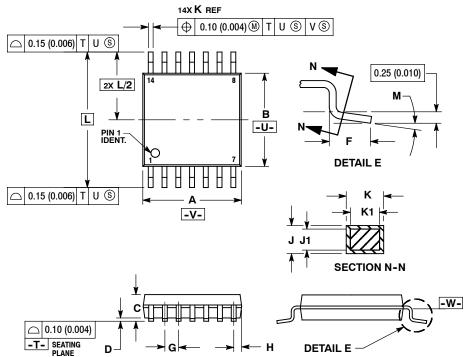


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	NATE LEIN	IETERS	INC	HES
	WILLIN	IEIEKS	INC	псо
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

# **PACKAGE DIMENSIONS**

# **TSSOP DT SUFFIX** CASE 948G-01 ISSUE O



#### NOTES:

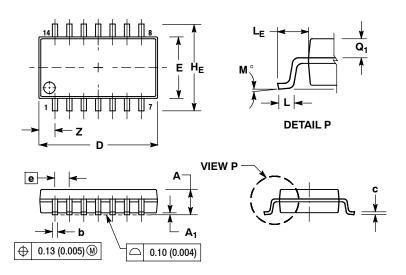
- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BE 0.08 (0.03) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

#### PACKAGE DIMENSIONS

# SO-14 M SUFFIX CASE 965-01 ISSUE O



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M. 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR

  REFERENCE ONLY
- REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		1.42		0.056

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